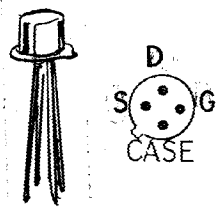
MICRO ELECTRONICS

2N4416,A

N-CHANNEL FET

CASE TO-72



2N4416 and 2N4416A are N-channel field-effect transistors designed for general purpose amplifier and chopper applications.

ABSOLUTE MAXIMUM RATINGS :

		2N4416	2N4416A
Drain-Gate Voltage	V_{DG}	30V	35V
Drain-Source Voltage	V_{DS}	30V	35V
Reverse Gate-Source Voltage	V_{GS}	30V	35V
Gate Current	I_G	10mA	
Total Power Dissipation @ T_A=25°C	Ptot	300mW	
Operating Junction & Storage Temperature	Tj,Tstg	-65 to +200°C	

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise specified)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Gate-Source Breakdown Voltage	BV_{GSS}			V	I_G=1μA V_{DS}=0
2N4416		30			
2N4416A		35			
Gate-Source Forward Voltage	V_{GSF}		1	V	I_G=1mA V_{DS}=0
Gate Reverse Current	I_{GSS}		100	pA	V_{GS}=20V V_{DS}=0
			200	pA	V_{GS}=20V V_{DS}=0 T_A=150°C
Gate-Source Cutoff Voltage	$V_{GS(off)}$			V	V_{DS}=15V I_D=1nA
2N4416			6		
2N4416A		2.5	6		
Gate-Source Voltage	V_{GS}	1	5.5	V	V_{DS}=15V I_D=0.5mA
Zero-Gate Voltage Drain Current	I_{DSS}	5	15	mA	V_{DS}=15V V_{GS}=0
Small-Signal Common-Source Forward Transfer Addmittance	Yfs	4.5	7.5	mmho	V_{DS}=15V V_{GS}=0 f=1KHz

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